MICROWAVE POWER GAN HEMT **TGI5059-120L**

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

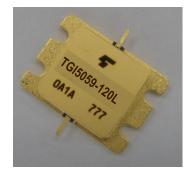
FEATURES

- •BROAD BAND INTERNALLY MATCHED HEMT •HIGH POWER
 - Pout= 51.0dBm at Pin= 42.0dBm

·HIGH GAIN

GL= 13.5dB at Pin= 20.0dBm

- •LOW INTERMODULATION DISTORTION IM3(Min.)= -25dBc at Pout= 44.0dBm Single Carrier Level
- ·HERMETICALLY SEALED PACKAGE



CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power	Pout	VDS= 24V IDSset= 4.0A f = 5.0 to 5.9GHz @Pin= 42dBm	dBm	50.0	51.0	
Drain Current	IDS1		А		11.0	12.0
Power Added Efficiency	ηadd		%		40	
Linear Gain	GL	@Pin= 20dBm	dB	12.5	13.5	
Gain flatness	ΔG		dB			±0.8
3rd Order Intermodulation Distortion	IM3	Two-Tone Test @Po=44.0dBm, ∆f= 5MHz (Single Carrier Level)	dBc	-25	-27	
Drain Current	IDS2		А			8.0
Channel Temperature Rise	∆Tch	(VDS X IDS + Pin – Pout) X Rth(c-c)	°C		120	140

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

Recommended Gate Resistance (Rg): 28 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 5V IDS= 10.0A	S	_	8.0	_
Pinch-off Voltage	VGSoff	VDS= 5V IDS= 46mA	V	-2.6	-4.0	-6.0
Saturated Drain Current	IDSS	VDS= 5V VGS= 0V	А		28	
Gate-Source Breakdown Voltage	VGSO	IGS= -20mA	V	-10		
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		0.6	0.8

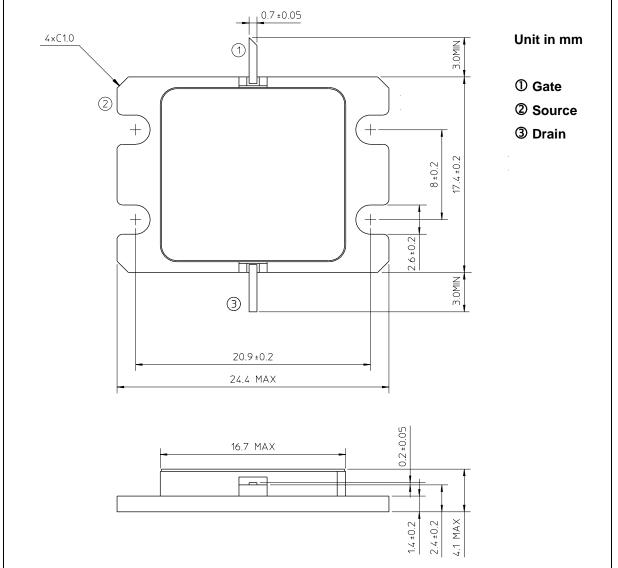
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MICROWAVE SEMICONDUCTOR TECHNICAL DATA

ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	50
Gate-Source Voltage	VGS	V	-10
Drain Current	IDS	А	18.0
Total Power Dissipation (Tc= 25°C)	PT	W	280
Channel Temperature	Tch	°C	250
Storage Temperature	Tstg	°C	-65 to +175

PACKAGE OUTLINE (7-AA06A)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

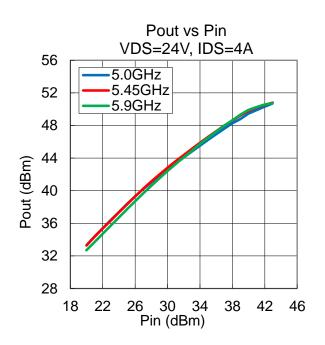
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

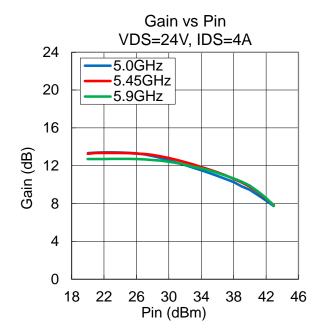
MICROWAVE POWER GaN HEMT TGI5059-120L

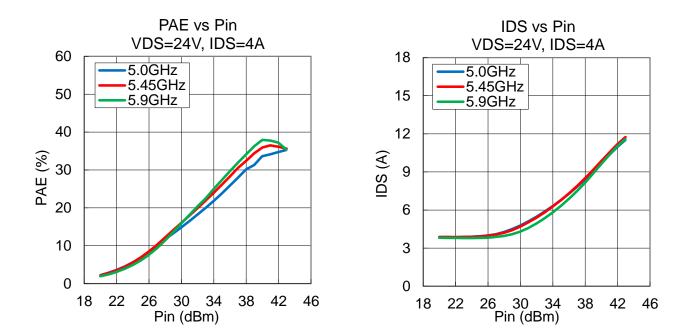
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

Pout , Gain , PAE , IDS vs. Pin

VDS= 24 V, IDSset= 4.0 A, f= 5.0, 5.45, 5.9 GHz, Ta= +25 °C





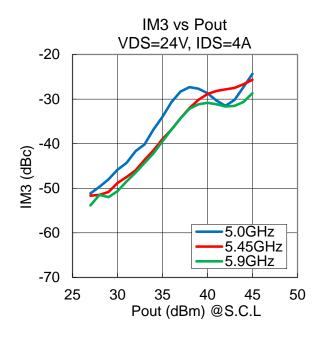


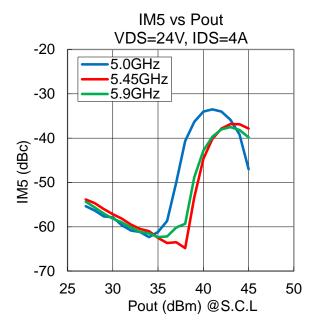
- MICROWAVE SEMICONDUCTOR TECHNICAL DATA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·IM3, IM5 vs. Pout

VDS= 24 V, IDSset= 4.0 A, f= 5.0, 5.45, 5.9 GHz, Δf= 5 MHz , Ta= +25 °C



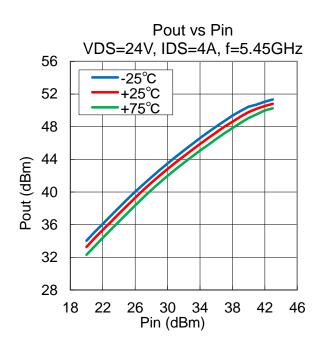


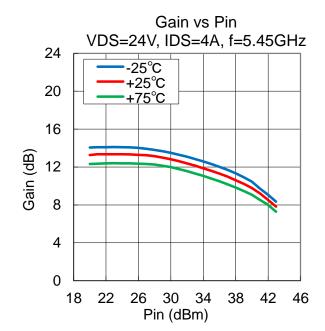
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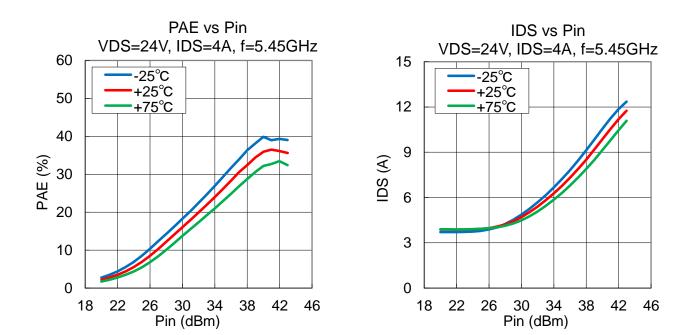
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·Pout , Gain , PAE , IDS vs. Pin vs. Temperature

VDS= 24 V, IDSset= 4.0 A, f= 5.45 GHz, Ta= -25, +25, +75 °C



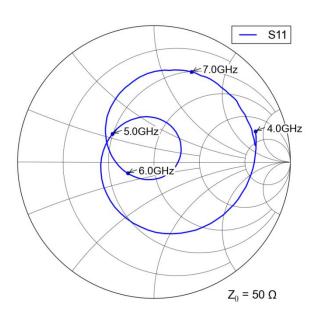


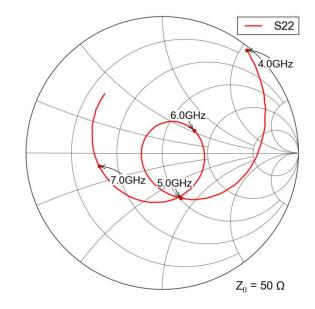


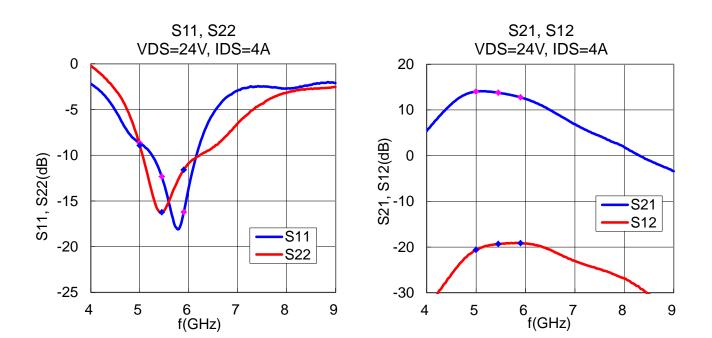
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·S-Parameters

VDS= 24 V, IDSset= 4.0 A, f= =4.0 to 9.0 GHz, Ta= +25 °C







- MICROWAVE SEMICONDUCTOR TECHNICAL DATA

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MICROWAVE SEMICONDUCTOR TECHNICAL DATA

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